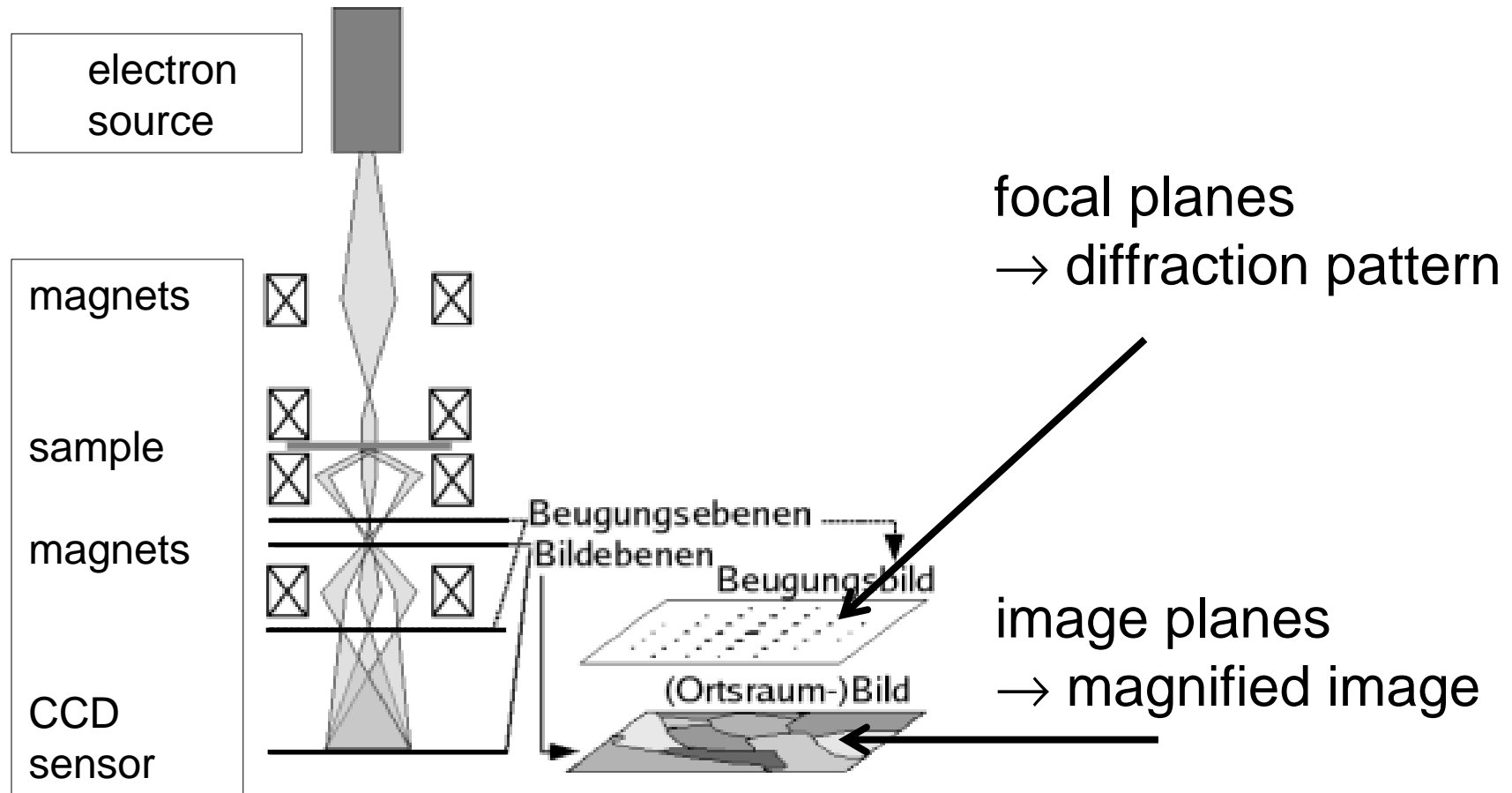


8. Transmission Electron Microscopy TEM

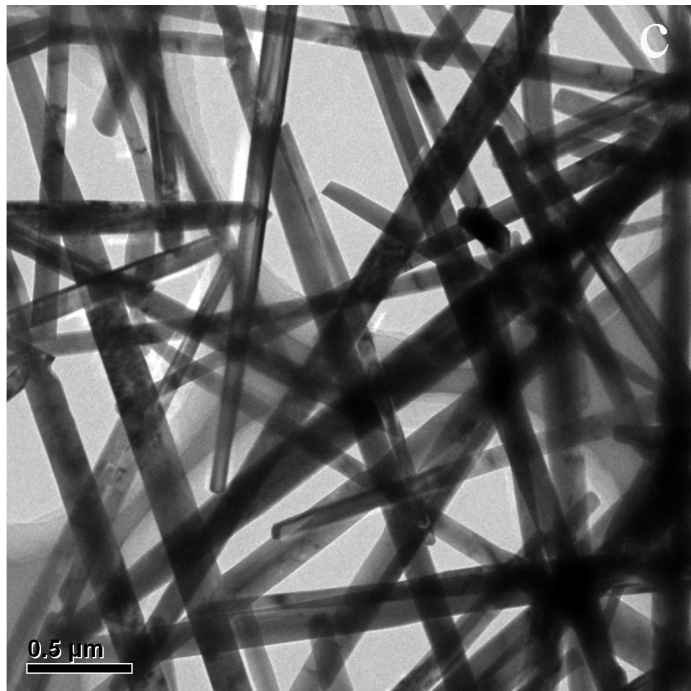


Electron beam passes the sample.
→ very thin sample

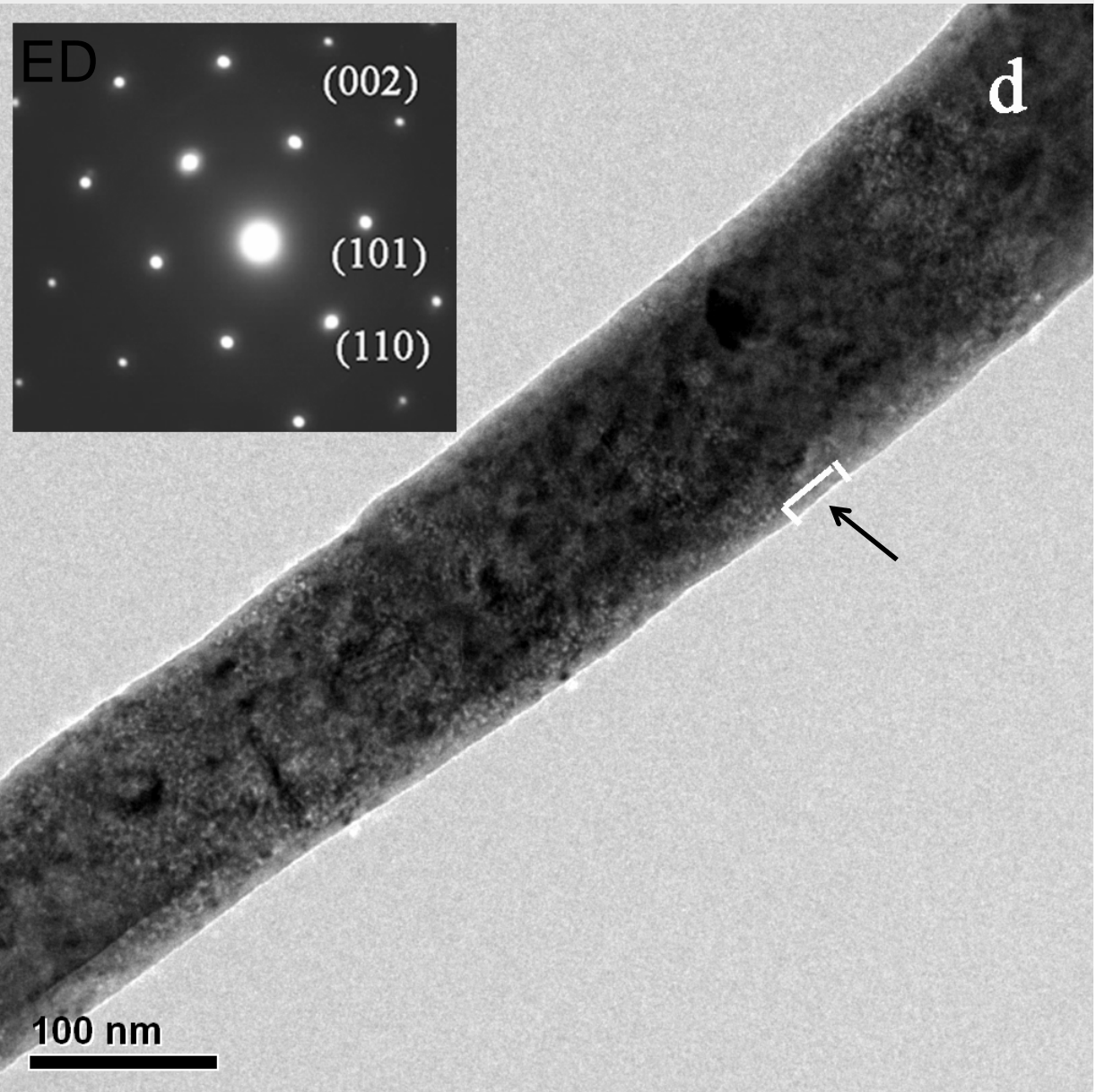
Excellent resolution.
→ down to atomic scale

8. Transmission Electron Microscopy TEM

Electron Diffraction



magnified images

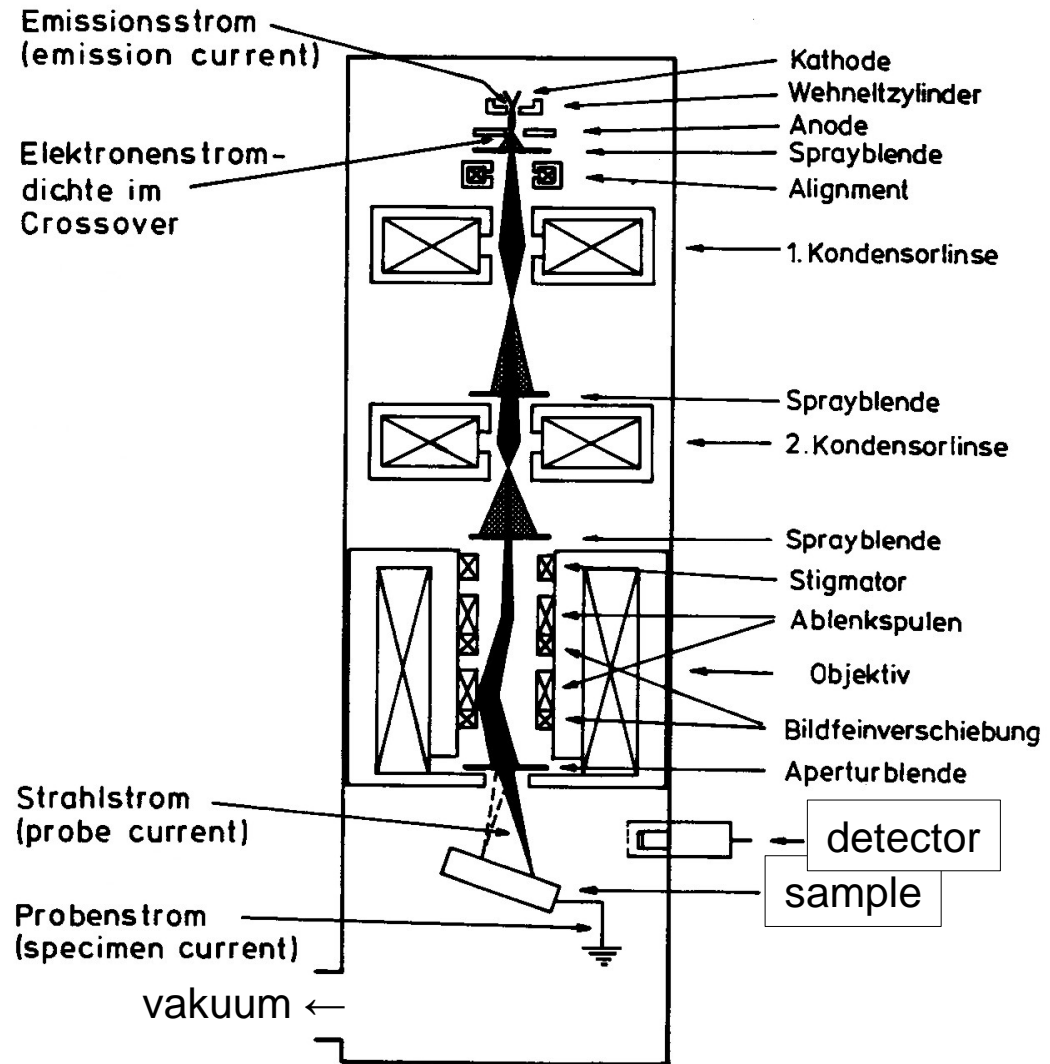


9. Scanning Electron Microscopy SEM

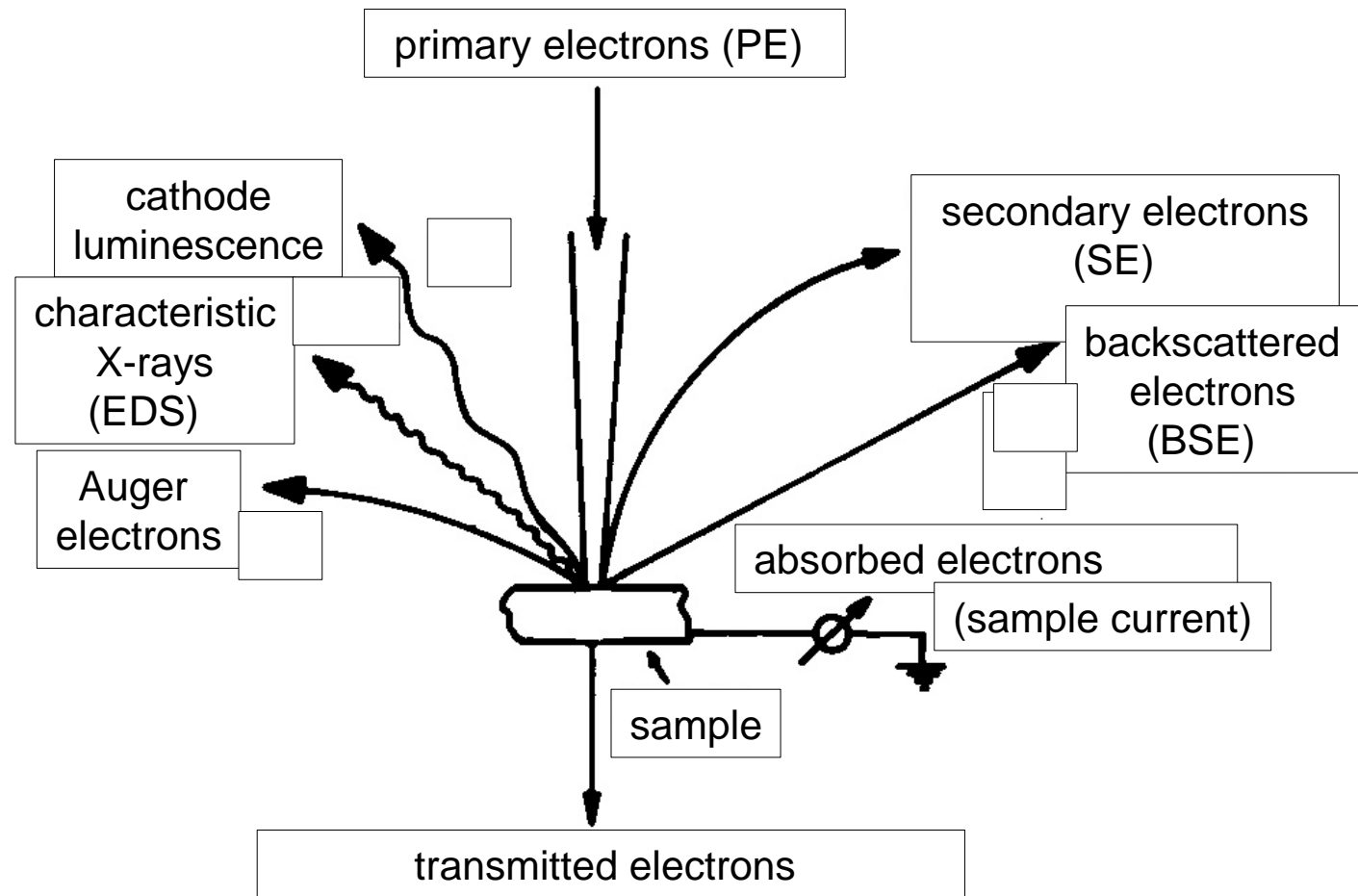
The sample (in vacuum) is scanned by the electron beam.

The electrons emitted from the sample are detected.

- variable sample size
- simple sample preparation
- limited resolution (~ 50 nm)



9. SEM



primary electrons (PE)

backscattered electrons (BSE) elastic scattering $E_{BSE} \approx E_{PE}$

secondary electrons (SE) inelastic scattering $E_{SE} < 50 \text{ eV}$

characteristic X-rays element analysis (EDS)

9. SEM

$$E_{PE} \sim E_{BSE}$$

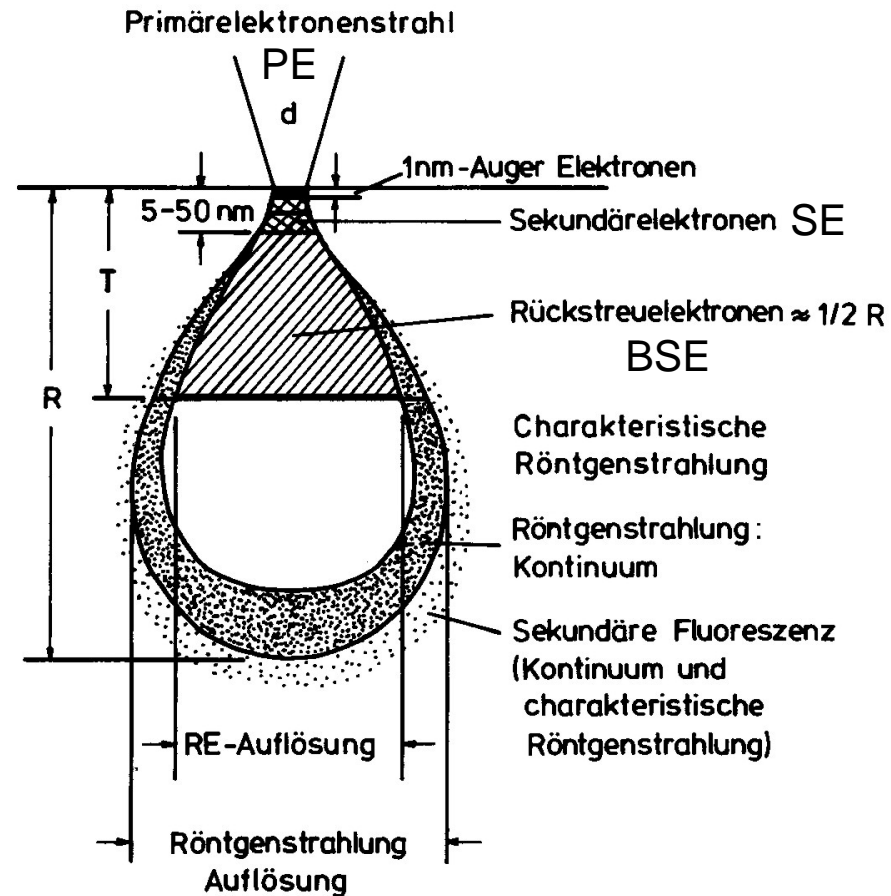
$$E_{Auger} < E_{SE} \ll E_{BSE}$$

PE beam diameter
 $d \sim 0.005 \text{ nm}$

resolution ———

SE $\sim 10 \text{ nm}$

BSE $> 50 \text{ nm}$



Reichweite R der PE und Austrittstiefen der verschiedenen Signale im REM

— R : Reichweite der PE

— T : Austrittstiefe der RE

— Auflösungsgrenze der RE $\approx 1/2 R$

— Auflösungsgrenze der Röntgenstrahlung \approx Wechselwirkungsvolumen

— Auflösungsgrenze der sekundären Fluoreszenz \gg Wechselwirkungsvolumen

9. SEM interaction volume

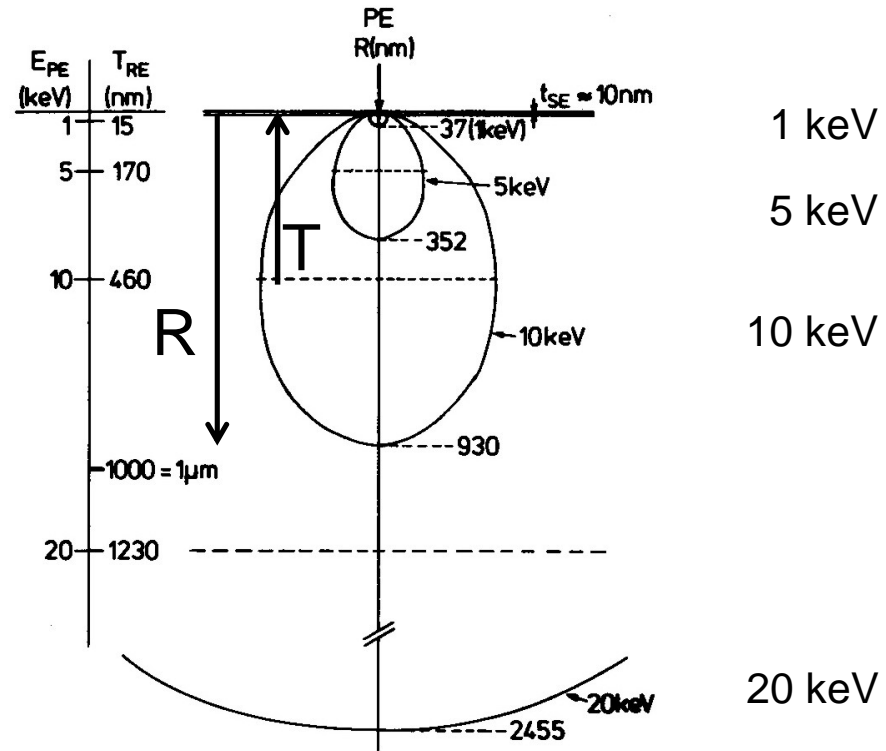
penetration depth (R)
of PE

and

escape depth (T)
of BSE

$$T \approx R / 2$$

aluminum for
various PE energies



Reichweite R, Wechselwirkungsvolumen und Austrittstiefe T in Al für E_{PE} von 1, 5, 10, 20 keV
 —: Reichweite R der PE, ---: Austrittstiefe T der RE

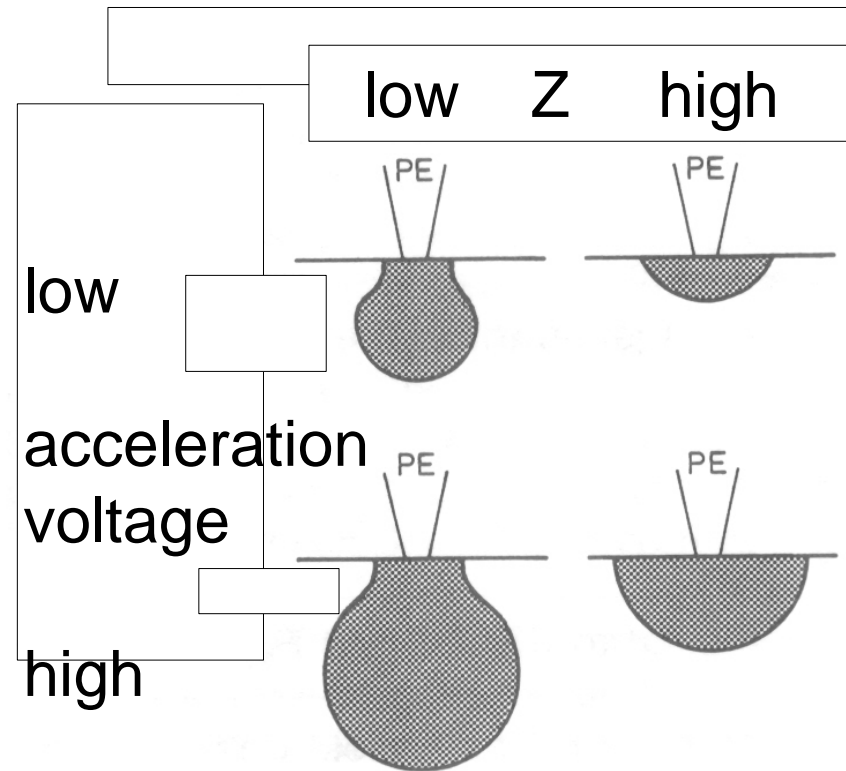
9. SEM interaction volume

PE energy

- penetration depth
- interaction volume

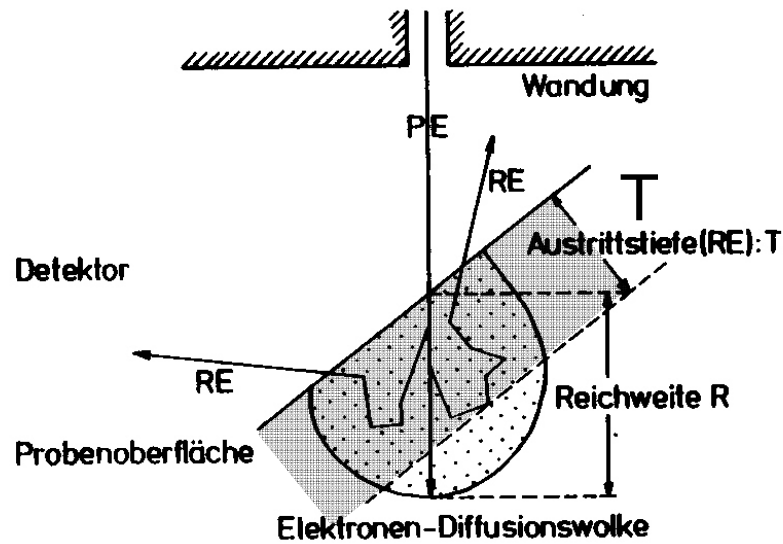
Electron density of sample

- shape and
- depth of interaction volume



9. SEM interaction volume

BSE

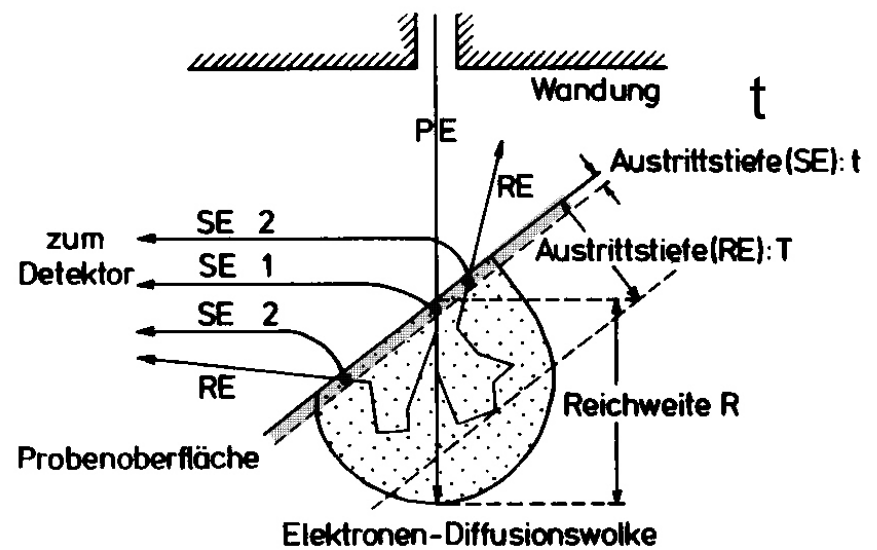


$$R \sim E_{PE}$$

$$T \approx R / 2$$

($T \approx 1-2 \mu\text{m}$)

SE

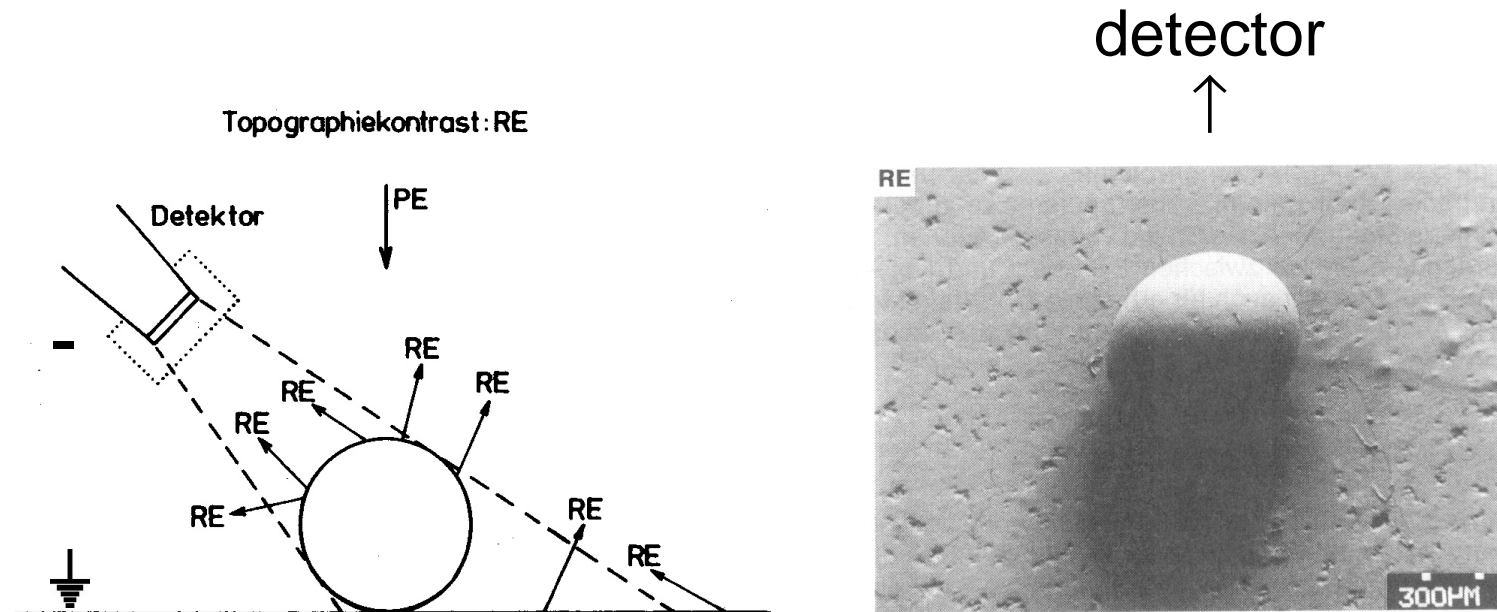


$$t \approx 5x \text{ free path length of SE}$$

metals: $t \approx 5 \text{ nm}$

isolators: $t \approx 50 \text{ nm}$

9. SEM topography for BSE



$$E_{PE} \approx E_{BSE} \text{ (typical 10 – 25 keV)}$$

shadow effect

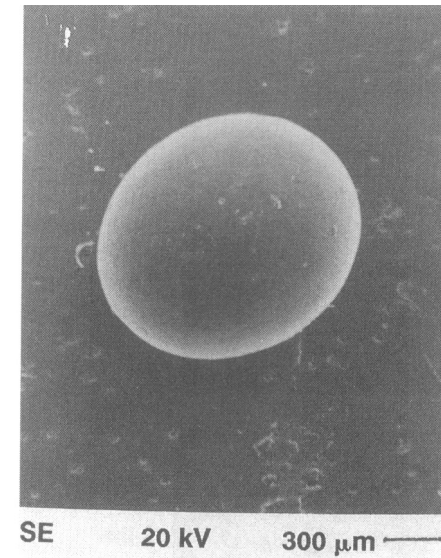
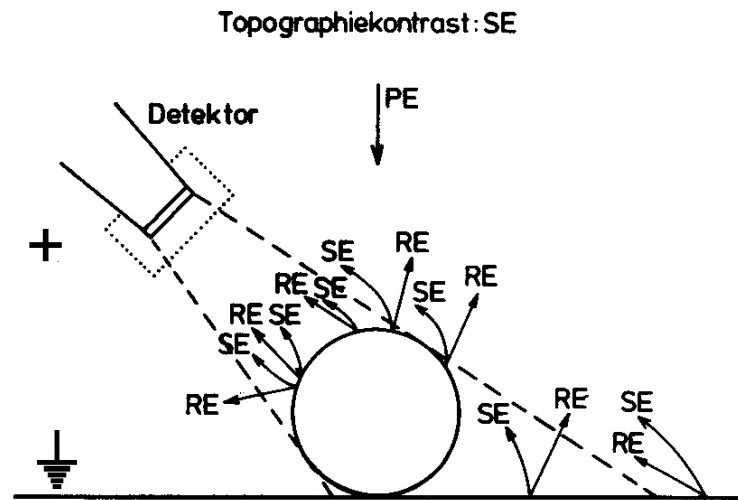
BSE: straight flight path, weak deflection by electric field

→ bright surface towards detector

→ shadow at back side

Negative voltage on detector keeps SE away.

9. SEM topography for SE



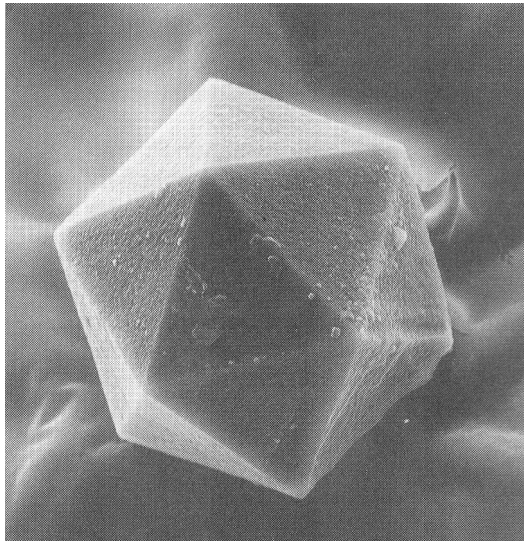
$$E_{SE} < 50 \text{ eV}$$

edge effect

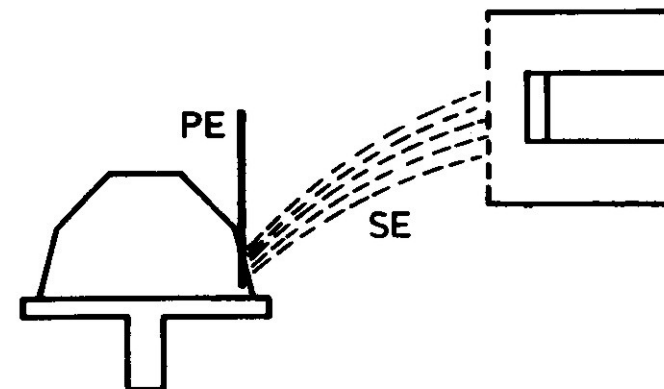
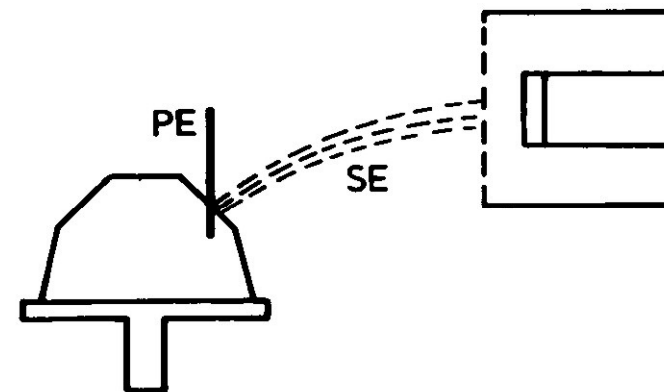
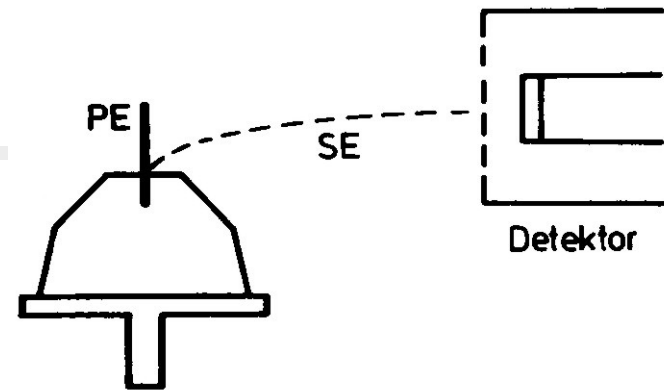
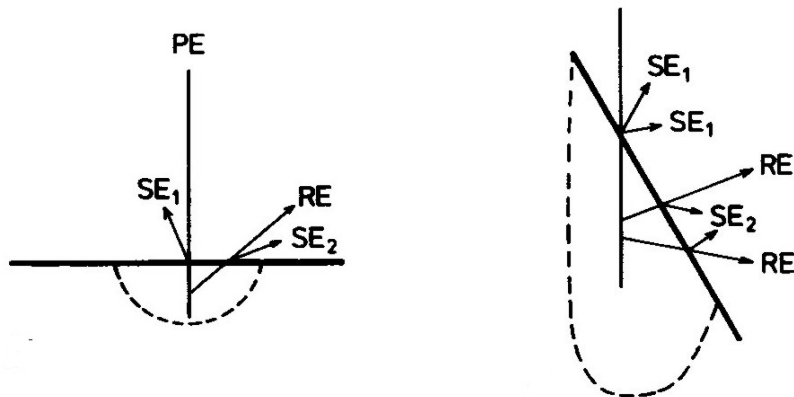
SE: curved flight path, strong deflection by electric field
The surface to volume ratio determines the SE intensity.
→ bright edge

Positive voltage attracts SE towards detector.

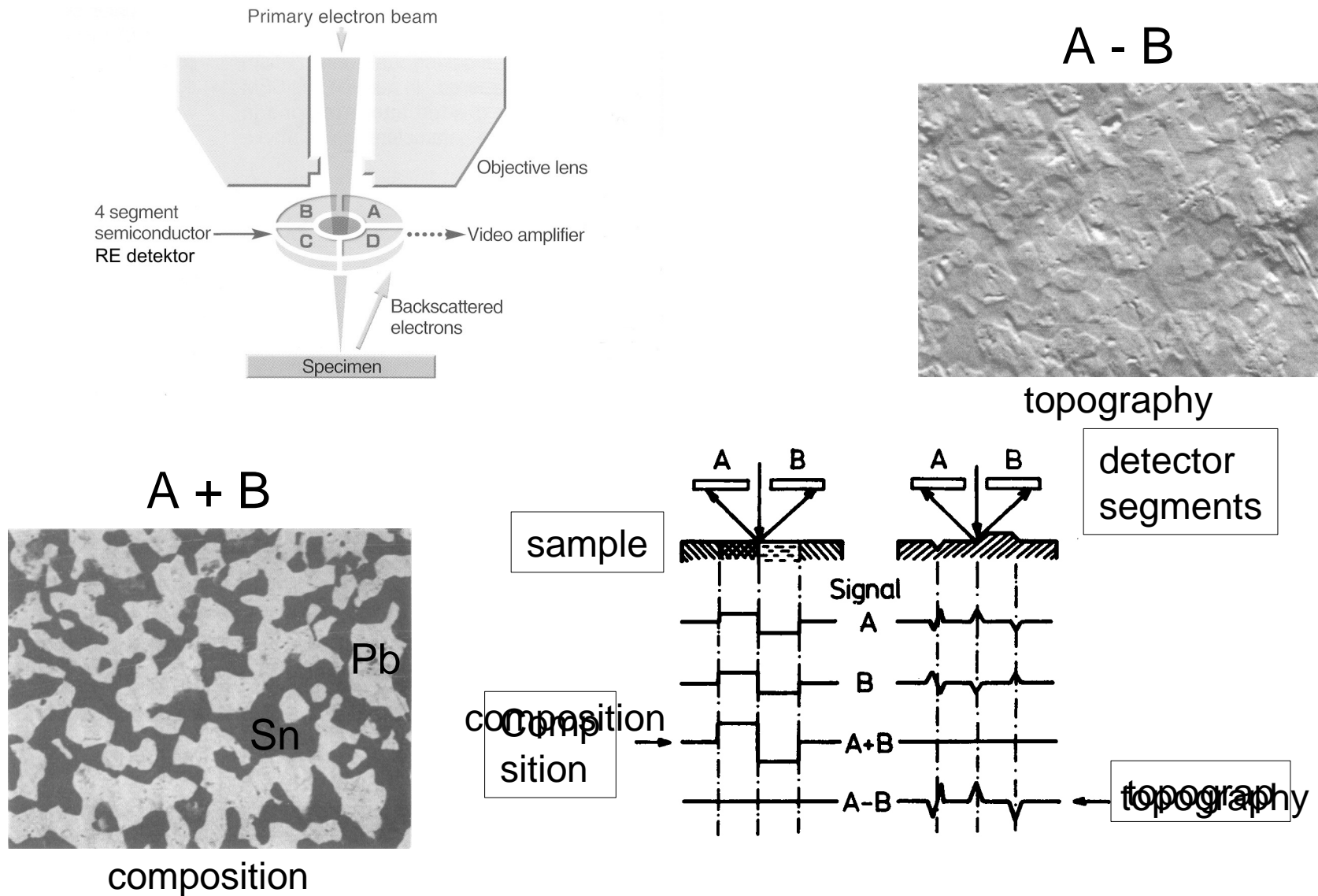
9. SEM topography SE



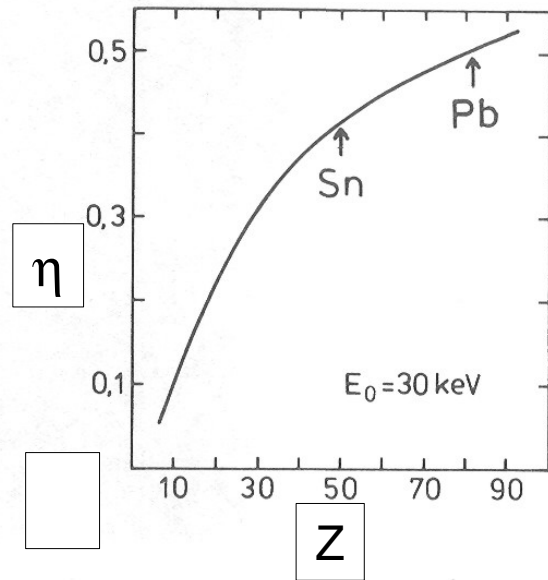
SE signal depends on surface inclination.



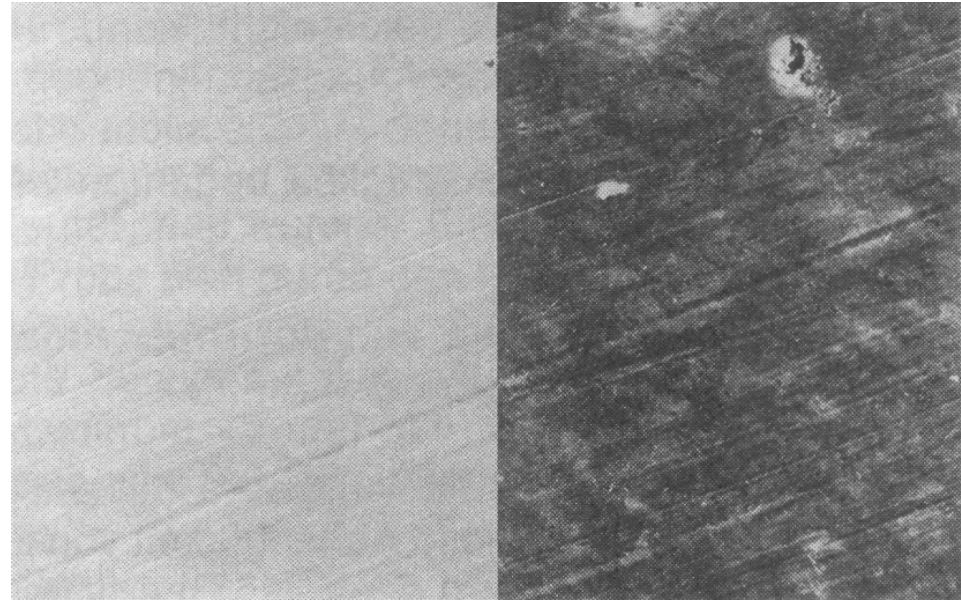
9. BSE enhanced composition or topography contrast



9. Composition contrast



interaction coefficient η
→ electron density



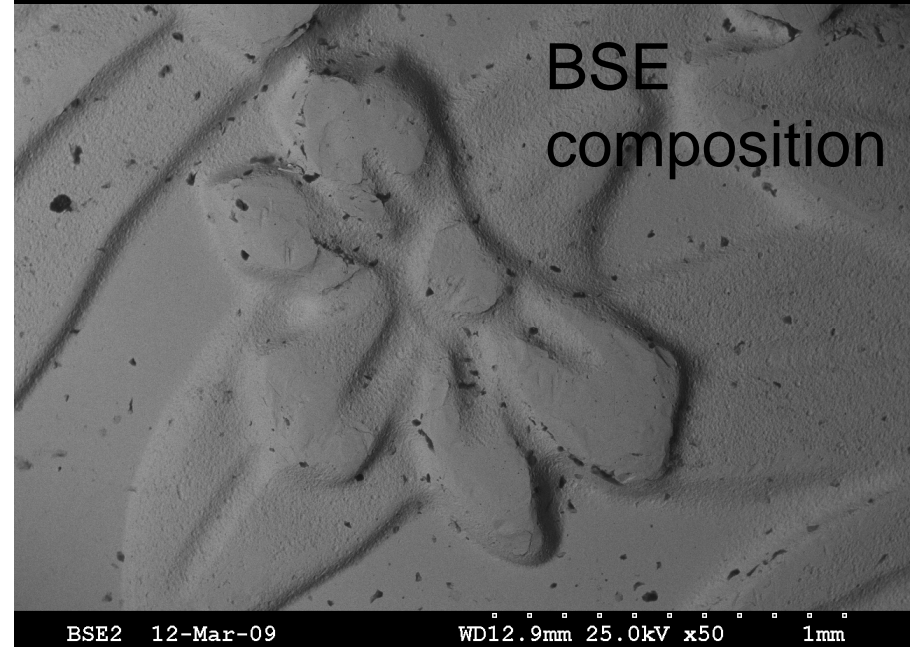
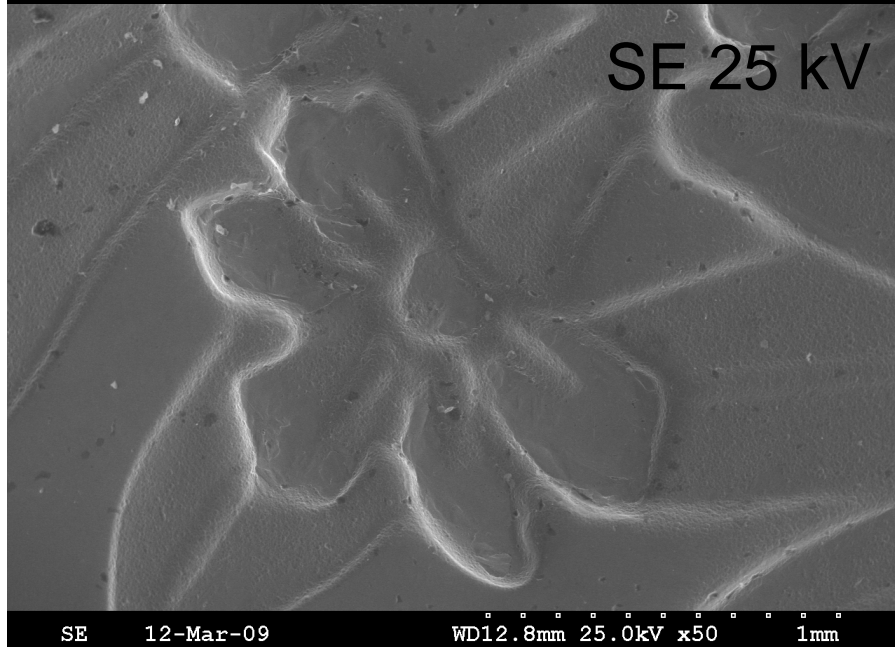
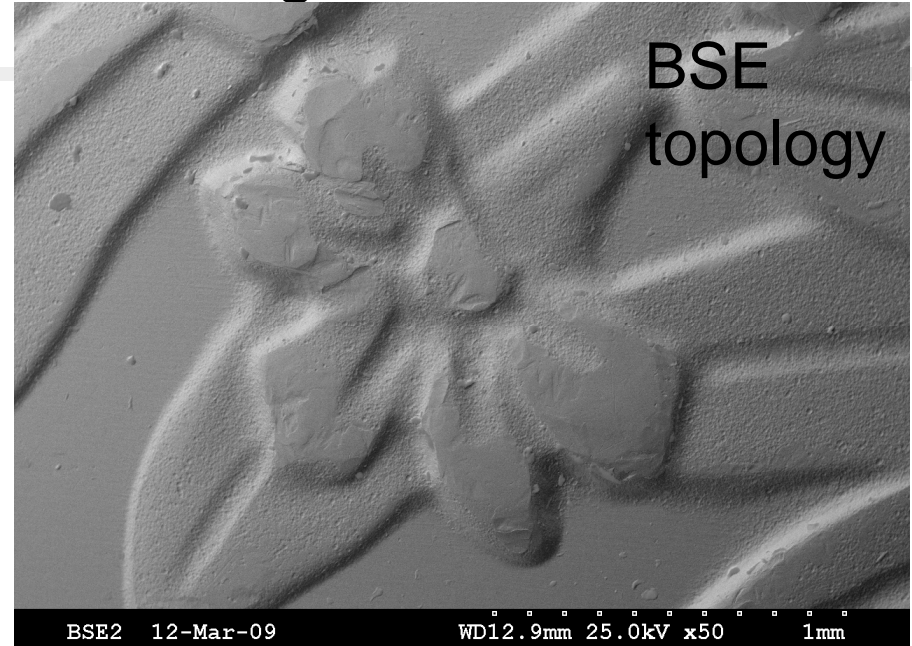
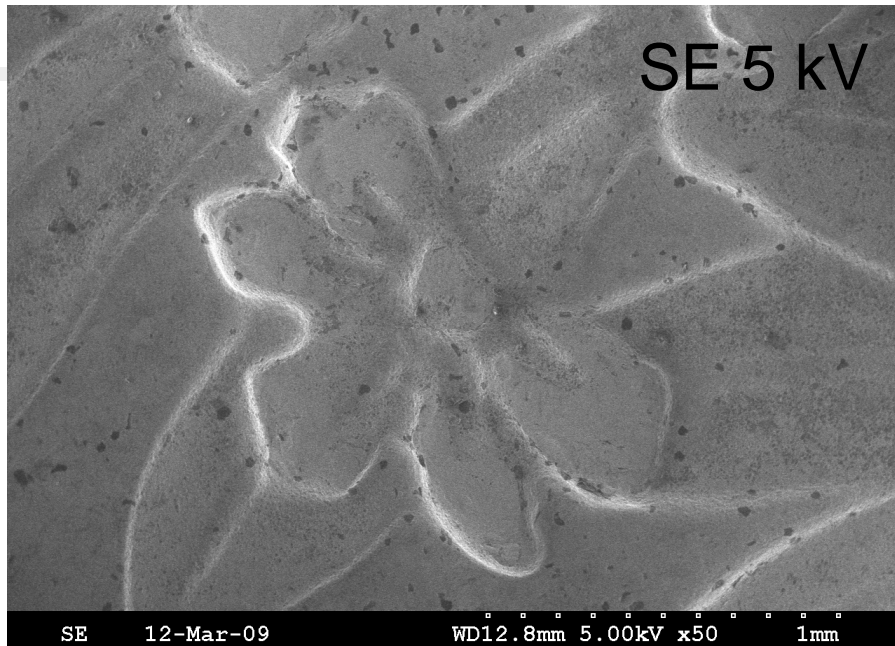
Au sputtered

C sputtered

heavy elements
→ bright

light elements
→ dark

9. SE versus BSE images



9. Summary EM

- TEM images with highest magnification
electron diffraction
demanding sample preparation
- SEM SE images (standard)
BSE images - composition
- topography
EDS element analysis
simple sample preparation
(flexible in size and shape)